



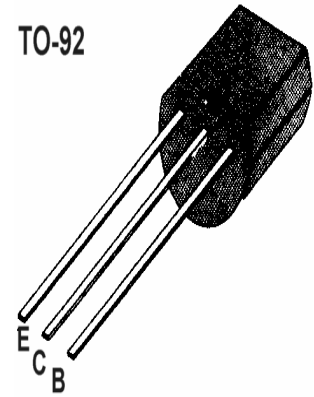
《风光欣》技术资料

M28S

NPN EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EB0}	5	V
Collector Current	I_{cm}	1.5	A
Collector Dissipation	P	1	W
Junction Temperature	T_j	150	
Storage Temperature	T_{STG}	-55 ~150	



ELECTRICAL CHARACTERISTICS ($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV_{CB0}	$I_c=100 \mu A, I_E=0$	40			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_c=1mA, I_B=0$	25			V
Emitter Base Breakdown Voltage	BV_{EB0}	$I_E=100 \mu A, I_c=0$	5			V
Collector Cut-off Current	I_{CB0}	$V_{CB}=35V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=6V, I_c=0$			100	nA
Collector -Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=800mA, I_B=80mA$			0.5	V
Base -Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c=800mA, I_B=80mA$			1.2	V
DC Current Gain	HFE1	$V_{CE}=1V, I_c=100mA$	500		1000	
	HFE2	$V_{CE}=1V, I_c=500mA$				
Transition Frequency	f_T	$V_{CE}=10V, I_c=50mA$	100			MHz
Output Capacitance	C_{OB}	$F=1MHz, V_{CB}=10V, I_E=0$			8	PF

Hfe 分档及其标志

分档	C	D	D2
HFE(2)	500~700	700~1000	>1000